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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: **Krutko et al.**
Appl. No.: 10/783,825
Filed: February 20, 2004
TC/A.U.: 2817
Examiner: not yet assigned
Docket No.: 060999-0181
Customer No.: **009629**
For: **MONOLITHICALLY FABRICATED HBT
AMPLIFICATION STAGE WITH CURRENT LIMITING
FET**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), Applicant brings to the attention of the Examiner the documents listed on the attached PTO-1449. This Information Disclosure Statement is being filed before the mailing of the first Office Action on the merits.

A copy of each listed document is attached except for U.S. Patents. Applicant respectfully requests that the Examiner consider the listed document and evidence that consideration by making appropriate notations on the attached form.


This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that the listed document is material or constitutes "prior art." If it should be determined that the listed document does not constitute "prior art" under United States law, Applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of such document. Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed document, should the document be applied against the claims of the present application.

If there is any fee due in connection with the filing of this Statement, please charge the fee to our Deposit Account No. 50-0310.

Respectfully submitted,

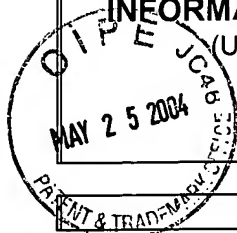
Morgan, Lewis & Bockius LLP

Date: May 25, 2004



Steven K. Fukuda (Reg. No. 44,690)
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Attachments

**INFORMATION DISCLOSURE CITATION**

(Use several sheets if necessary)

PTO Form 1449

Attorney Docket No.

60999-181

Serial No.

10/783,825

Applicants

Krutko et al.

Filing Date

February 20, 2004

Group

2817

U.S. PATENT DOCUMENTS

| *Examiner Initial | | Document Number | Date | Name | Class | Sub Class | Filing Date |
|-------------------|-----|-----------------|------|------|-------|-----------|-------------|
| | A01 | | | | | | |
| | A02 | | | | | | |
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FOREIGN PATENT DOCUMENTS

| | | Document Number | Date | Country | Class | Sub Class | <u>Translation</u> | |
|--|-----|-----------------|------|---------|-------|-----------|--------------------|----|
| | | | | | | | YES | NO |
| | B01 | | | | | | | |
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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| | C05 | K. Itakura, Y. Shimamoto, T. Ueda, S. Katsu, D. Ueda, " A GaAs Bi-FET technology for large scale integration", IEDM Tech. Dig., 1989, p. 389. |



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| C08 | J. Jang, E. C. Kan, T. Arnborg, T. Johansson, R. Dutton, "Characterization of RF Power BJT and Improvement of Thermal Stability with Nonlinear Base Ballasting", 1998 IEE, pg. 1428. |

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| Examiner | Date Considered |
| Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |